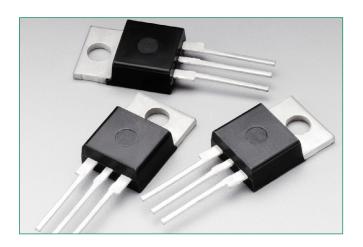
Surface Mount - 400V - 800V







Additional Information







Accessories



Samples

Description

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required. The MAC9xG is designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

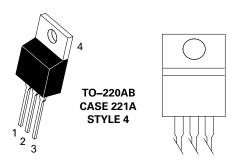
Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 8.0 Amperes RMS at 100°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dv/dt 500 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220 Package
- High Commutating di/dt 6.5 A/ms minimum at 125°C
- These Devices are Pb-Free and are RoHS Compliant

Functional Diagram



Pin Out





Surface Mount - 400V - 800V

Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = 40^{\circ}$ to 125°C)	MAC9D MAC9M MAC9N	V _{DRM} , V _{RRM}	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_{\rm c}$ = 10	I _{T (RMS)}	8.0	А	
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T_J = 125°C)	I _{TSM}	80	А	
Circuit Fusing Consideration (t = 8.3 ms)		l ² t	26	A²sec
Peak Gate Power (Pulse Width $\leq 1.0 \mu s$, $T_c = 80^{\circ}C$)	P _{GM}	16	W	
Average Gate Power (t = 8.3 ms , $T_c = 80^{\circ}\text{C}$)		$P_{G(AV)}$	0.35	W
Operating Junction Temperature Range		T _J	-40 to +125	°C
Storage Temperature Range	T_{stg}	-40 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{eJC} R _{eJA}	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purpose: 10 seconds	s, 1/8" from case for	T _L	260	°C

Electrical Characteristics - OFF (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T, = 25°C	I _{DRM} ,	-	-	0.01	mΛ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	T _J = 125°C	I	-	-	2.0	mA

Electrical Characteristics - ON (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On-State Voltage (Note 2) ($I_{TM} = \pm 11 \text{ A}$)		V_{TM}	_	1.2	1.6	V
Gate Trigger Current	MT2(+), G(+)		10	16	50	
(Continuous dc)	MT2(+), G(-)	I _{GT}	10	18	50	mA
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)		10	22	5.0	
Holding Current ($V_D = 12 \text{ V}$, Gate Open, Initiating Current = $\pm 150 \text{ mA}$))	I _H	-	30	50	mA
	MT2(+), G(+)		_	20	50	
Latching Current $(V_D = 24 \text{ V, I}_C = 50 \text{ mA})$	MT2(+), G(-)	I	_	30	80	mA
(V _D = 2 1 V, I _G = 33 11) V	MT2(-), G(-)		_	20	50	
0 . T:	MT2(+), G(+)		0.5	0.69	1.5	
Gate Trigger Voltage $(V_D = 12 \text{ V}, R_I = 100 \Omega)$	MT2(+), G(-)	$V_{\rm GT}$	0.5	0.77	1.5	V
(V _D = 12 V, 11 _L = 100 32)	MT2(-), G(-)		0.5	0.72	1.5	
0 . N . T	MT2(+), G(+)		0.2	_	_	
Gate Non-Trigger Voltage $(V_D = 12 \text{ V}, R_L = 100 \Omega, T_J = 125^{\circ}\text{C})$	MT2(+), G(-)	V_{gD}	0.2	_	_	V
	MT2(-), G(-)		0.2	_	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.





^{1.} V_{DMA} and V_{BMA} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Surface Mount – 400V - 800V

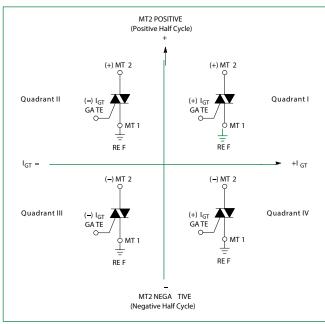
Dynamic Characteristics

Characteristic	Symbol	Min	Max	Unit
Rate of Change of Commutating Current See Figure 10. ($V_D = 400 \text{ V}$, $I_{TM} = 4.4 \text{ A}$, Commutating dv/dt = 18 V/ μ s, Gate Open, $T_J = 125 ^{\circ}$ C, $f = 250 \text{ Hz}$, No Snubber) $C_I = 10 \ \mu\text{F}$ $L_I = 40 \text{ mH}$	di/dt _(C)	6.5	-	A/ms
Critical Rate of Rise of Off-State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform, Gate open, T_J = 125°C)$	dV/dt	500	_	V/µs

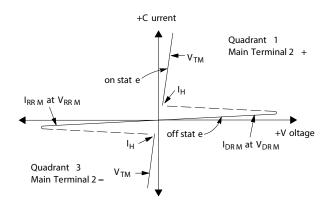
Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac



All polarities are referenced to MT1. With in–phase signals (using standard AC lines) quadrants I and III are used



Surface Mount – 400V - 800V

Figure 1. RMS Current Derating

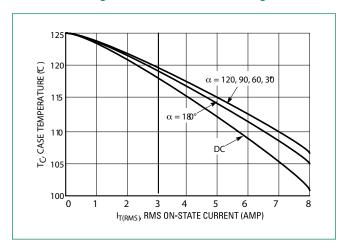


Figure 3. On-State Characteristics

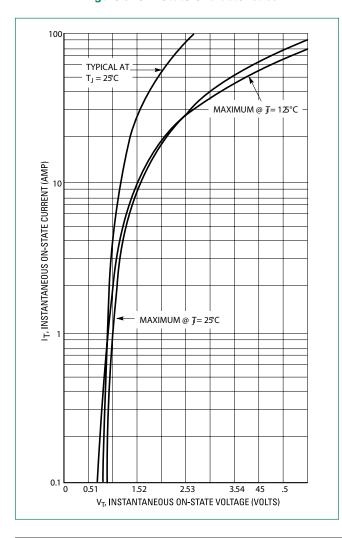


Figure 2. On-State Power Dissipation

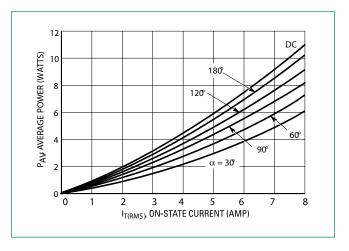


Figure 4. Thermal Response

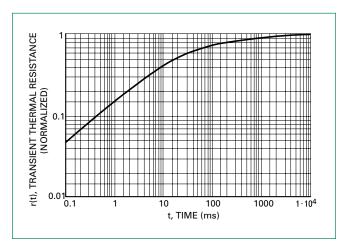
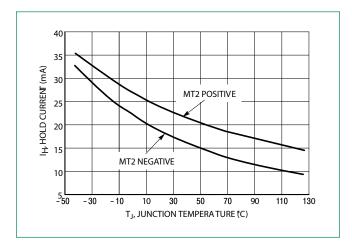


Figure 5. Hold Current Variation





Surface Mount - 400V - 800V

Figure 6. Gate Trigger Current Variation

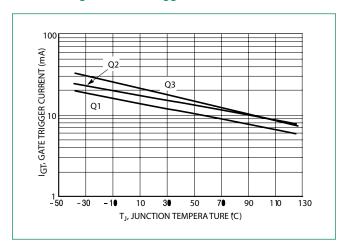


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential)

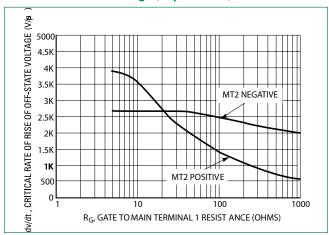


Figure 7. Gate Trigger Voltage Variation

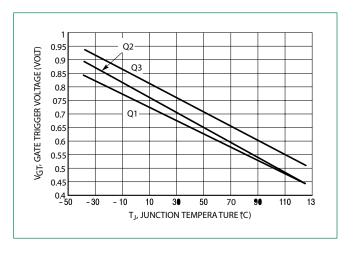


Figure 9. Critical Rate of Rise of Commutating Voltage

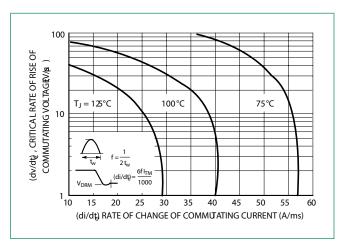
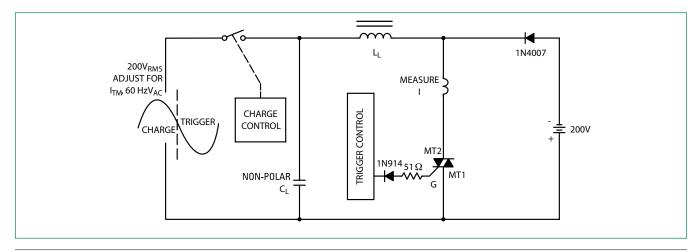


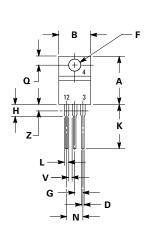
Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)

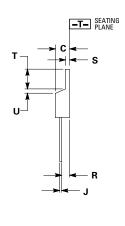




Surface Mount – 400V - 800V

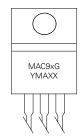
Dimensions





Part Marking System





- x =D, M, or N Y =Year
- M =Month
- A =Assembly Site XX =Lot Serial Code G =Pb-Free Package

D:	Incl	hes	Millim	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52

- Dimensioning and tolerancing per ansi y14.5m, 1982.
 Controlling dimension: inch.
- 3. Dimension z defines a zone where all body and lead irregularities are allowed.

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	No Connection			

Ordering Information

Device	Package	Shipping
MAC9DG	TO 000 A D	
MAC9MG	TO-220AB (Pb-Free)	1000 Units / Box
MAC9NG	(1 5 1100)	

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at http://www.littelfuse.com/disclaimer-electronics.



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Littelfuse:

MAC9NG MAC9DG MAC9MG